

DSS4160FDBQ

60V DUAL NPN LOW SAT TRANSISTOR IN DFN2020-6

Mechanical Data

BV_{CEO} > 60V

Features

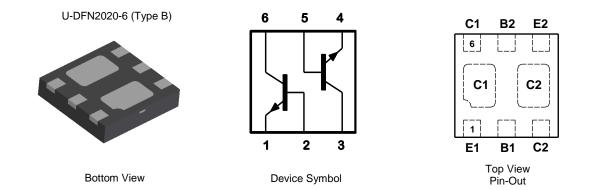
- I_C = 1A High Continuous Collector Current
- R_{CE(sat)} = 180mΩ for a Low Equivalent On-Resistance
- Low Saturation Voltage V_{CE(sat)} < 220mV @ 1A
- P_D up to 2.47W for Power-Demanding Applications
- R_{0JA} Efficient, 40% Lower than SOT26
- Low Profile 0.6mm High Package for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DSS4160FDBQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

- Package: U-DFN2020-6 (Type B)
- Package Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @
- Weight: 0.0065 grams (Approximate)

Application

- Load switches
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)



Ordering Information (Note 4)

| Product | Compliance | Marking | Reel Size (inches) | Tape Width (mm) | Quantity per Reel |
|---------------|------------|---------|--------------------|-----------------|-------------------|
| DSS4160FDBQ-7 | Automotive | 2B | 7 | 8 | 3,000 |

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information

U-DFN2020-6 (Type B)



- 2B = Product type Marking Code
- \overline{Y} = Year: 0~9
- W = Week: A~Z = 1~26 Week; A~Z = 27~52 Week;
 - Z Represents 52 and 53 Week
- X = A~Z: Internal Code



Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CBO} | 60 | V |
| Collector-Emitter Voltage | V _{CEO} | 60 | V |
| Emitter-Base Voltage | V _{EBO} | 7 | V |
| Continuous Collector Current | I _C | 1 | A |
| Peak Pulse Collector Current | I _{CM} | 1.5 | A |
| Base Current | IB | 300 | mA |
| Peak Base Current | I _{BM} | 1 | A |

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|---|----------------------------------|------------------|------|------|--|
| | (Note 5, 7) | | 405 | | |
| Power Dissipation | (Note 5, 8) | D | 510 | mW | |
| | (Note 6, 7) | PD | 1650 | | |
| | (Note 6, 8) | | 2470 | | |
| | (Note 5, 7) | | 308 | | |
| Thermal Resistance. Junction to Ambient | (Note 5, 8) | D | 245 | °C/W | |
| mermai Resistance, Junction to Ambient | (Note 6, 7) | R _{0JA} | 76 | C/W | |
| | (Note 6, 8) | | 51 | | |
| Thermal Resistance, Junction to Lead | (Note 9) | R _{θJL} | 18 | °C/W | |
| Operating and Storage Temperature Range | T _{J,} T _{STG} | -55 to +150 | °C | | |

ESD Ratings (Note 10)

| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge – Human Body Model | ESD HBM | 4000 | V | ЗA |
| Electrostatic Discharge – Charged Device Model | ESD CDM | 1000 | V | C3 |

5. For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6 Same as Note (5), except the device is mounted with the collector pad on 28mm x 28mm (8cm²) 2oz copper. Notes:

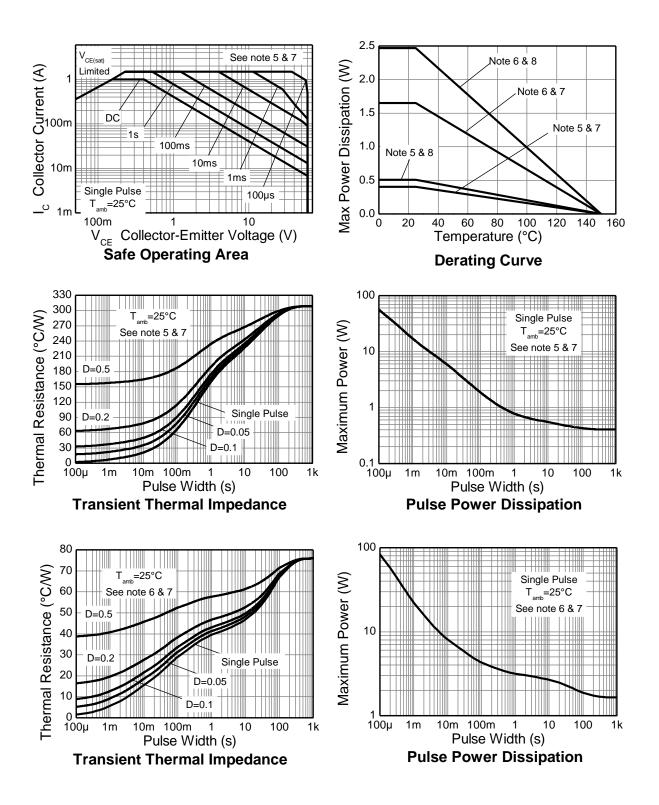
7. For a dual device with one active die.

8. For dual device with two active die running at equal power.

Thermal resistance from junction to solder-point (on the exposed collector pads).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





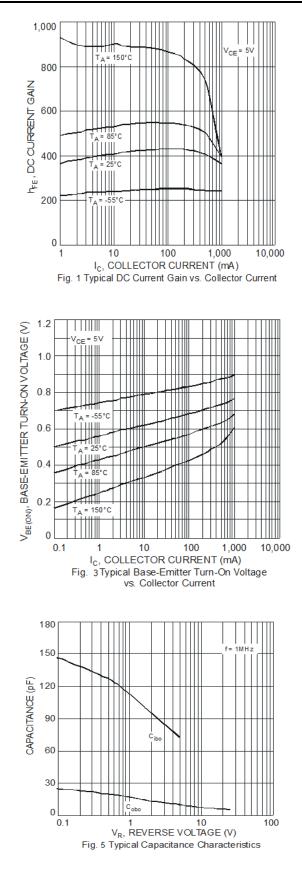
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

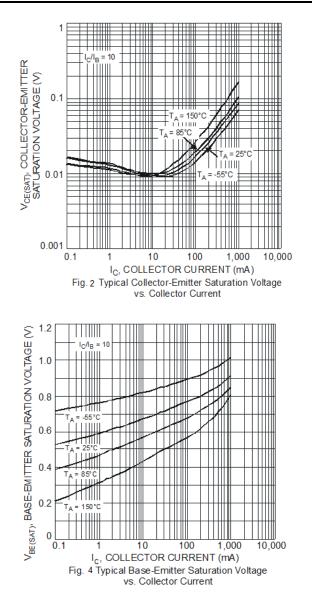
| Characteristic | Cumula al | Min | Tran | Max | 11 | Test Conditions |
|--|----------------------|-----|------|-----|------|---|
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Conditions |
| Collector-Base Breakdown Voltage | BV _{CBO} | 60 | | — | V | $I_{\rm C} = 100 \mu A$ |
| Collector-Emitter Breakdown Voltage (Note 11) | BV _{CEO} | 60 | _ | | V | $I_{C} = 10 \text{mA}$ |
| Emitter-Base Breakdown Voltage | BVEBO | 7 | — | | V | I _E = 100μA |
| Collector-Base Cutoff Current | 1 | | _ | 100 | nA | $V_{CB} = 48V, I_E = 0$ |
| | I _{CBO} | | — | 50 | μA | $V_{CB} = 48V, I_E = 0, T_A = +150^{\circ}C$ |
| Emitter-Base Cutoff Current | I _{EBO} | | _ | 100 | nA | $V_{EB} = 5.6V, I_{C} = 0$ |
| | | 290 | 430 | | | $V_{CE} = 2V, I_{C} = 100mA$ |
| DC Current Gain (Note 11) | h _{FE} | 150 | 220 | _ | _ | $V_{CE} = 2V, I_{C} = 500 \text{mA}$ |
| | | 70 | 110 | | | $V_{CE} = 2V, I_C = 1A$ |
| | V _{CE(sat)} | | 90 | 120 | | $I_{\rm C} = 500$ mA, $I_{\rm B} = 50$ mA |
| Collector-Emitter Saturation Voltage (Note 11) | | | 170 | 220 | mV | $I_{\rm C} = 1$ A, $I_{\rm B} = 100$ mA |
| | | _ | 185 | 240 | | $I_{C} = 1A, I_{B} = 50mA$ |
| Equivalent On-Resistance (Note 11) | R _{CE(sat)} | | 180 | 240 | mΩ | $I_{\rm C} = 500$ mA, $I_{\rm B} = 50$ mA |
| | V _{BE(sat)} | | _ | 1 | V | $I_{\rm C} = 0.5 \text{A}, I_{\rm B} = 50 \text{mA}$ |
| Base-Emitter Saturation Voltage (Note 11) | | _ | _ | 1.1 | | $I_{\rm C} = 1$ A, $I_{\rm B} = 50$ mA |
| | | | _ | 1.1 | | $I_{\rm C} = 1$ A, $I_{\rm B} = 100$ mA |
| Base-Emitter Turn-on Voltage (Note 11) | V _{BE(on)} | | | 0.9 | V | $V_{CE} = 2V, I_{C} = 0.5A$ |
| Transition Frequency | fT | 90 | 175 | _ | MHz | V _{CE} = 10V, I _C = 50mA, f = 100MHz |
| Output (Collector) Capacitance | Cobc | | 4 | 6 | pF | $V_{CB} = 10V, f = 1MHz$ |
| Turn-On Time | t _{on} | _ | 105 | _ | ns | |
| Delay Time | td | | 15 | | ns | |
| Rise Time | tr | | 90 | _ | ns | $V_{CC} = 10V, I_{C} = 0.5A,$ |
| Turn-Off Time | t _{off} | _ | 540 | _ | ns | $I_{B1} = -I_{B2} = 25 \text{mA}$ |
| Storage Time | ts | | 410 | — | ns | 1 |
| Fall Time | tf | _ | 130 | _ | ns | 1 |

Note: 11. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

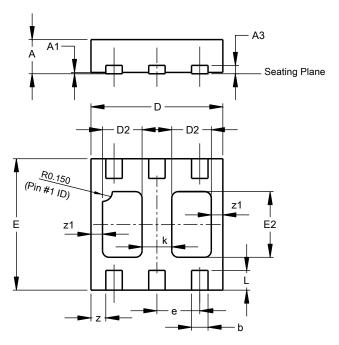






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



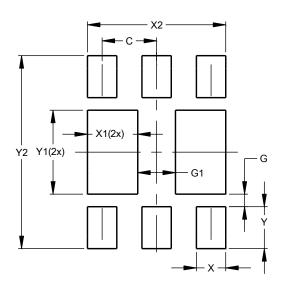
| U-DFN2020-6 Type B | | | | | | |
|-----------------------|----------------------|-------|-------|--|--|--|
| Dim | Min | Max | Тур | | | |
| Α | 0.545 | 0.605 | 0.575 | | | |
| A1 | 0.00 | 0.05 | 0.02 | | | |
| A3 | _ | - | 0.13 | | | |
| b | 0.20 | 0.30 | 0.25 | | | |
| D | 1.95 | 2.075 | 2.00 | | | |
| D2 | 0.50 | 0.70 | 0.60 | | | |
| е | - | - | 0.65 | | | |
| Е | 1.95 | 2.075 | 2.00 | | | |
| E2 | 0.90 | 1.10 | 1.00 | | | |
| k | _ | - | 0.45 | | | |
| L | 0.25 | 0.35 | 0.30 | | | |
| z | _ | - | 0.225 | | | |
| z1 | _ | _ | 0.175 | | | |
| All | All Dimensions in mm | | | | | |

U-DFN2020-6 (Type B)

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



| Dimensions | Value (in mm) |
|------------|------------------|
| С | 0.650 |
| G | 0.150 |
| G1 | 0.450 |
| Х | 0.350 |
| X1 | 0.600 |
| X2 | 1.650 |
| Y | 0.500 |
| Y1 | 1.000 |
| Y2 | 2.300 |



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